## Masashi Uematsu

List of Publications by Year in descending order

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1684188 1720034 8 193 5 7 citations h-index g-index papers 8 8 8 173 docs citations times ranked citing authors all docs

#	Article	IF	CITATIONS
1	Effect of fluorine on the suppression of boron diffusion in pre-amorphized silicon. Journal of Applied Physics, 2020, 128, 105701.	2.5	1
2	Effect of carbon situating at end-of-range defects on silicon self-diffusion investigated using pre-amorphized isotope multilayers. Japanese Journal of Applied Physics, 2016, 55, 036504.	1.5	1
3	Observation of silicon self-diffusion enhanced by the strain originated from end-of-range defects using isotope multilayers. Journal of Applied Physics, 2015, 118, 115706.	2.5	6
4	Behaviors of neutral and charged silicon self-interstitials during transient enhanced diffusion in silicon investigated by isotope superlattices. Journal of Applied Physics, 2009, 105, .	2.5	9
5	Charge states of vacancies in germanium investigated by simultaneous observation of germanium self-diffusion and arsenic diffusion. Applied Physics Letters, 2008, 93, .	3.3	56
6	Experimental Evidence of the Vacancy-Mediated Silicon Self-Diffusion in Single-Crystalline Silicon. Physical Review Letters, 2007, 98, 095901.	7.8	92
7	Transient Enhanced Diffusion of Boron in the Presence of Dislocations Produced by Amorphizing Implantation in Silicon. Japanese Journal of Applied Physics, 1998, 37, 5866-5869.	1.5	10
8	Quantitative Evaluation of Silicon Displacement Induced by Arsenic Implantation Using Silicon Isotope Superlattices. Applied Physics Express, 0, 1, 021401.	2.4	18